Product data sheet

1. General description

Hyperfast power diode in a SOD59 (2-lead TO-220AC) plastic package.

2. Features and benefits

- Fast switching
- Low reverse recovery current
- Low leakage current
- Low thermal resistance
- · Reduces switching losses in associated MOSFET or IGBT

3. Applications

- Active PFC in air conditioner
- · High frequency switched-mode power supplies
- Continuous Current Mode (CCM) Power Factor Correction (PFC)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit	
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse voltage			600		V	
$I_{F(AV)}$	average forward current	δ = 0.5; $T_{mb} \le$ 127 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3		10		А	
I _{FRM}	repetitive peak forward current	δ = 0.5; t_p = 25 μ s; $T_{mb} \le$ 127 °C; squarewave pulse		20		А	
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4			А		
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse			Α		
Symbol	Parameter	Conditions	Min Typ Max		Max	Unit	
Static ch	aracteristics						
V_{F}	forward voltage	I _F = 10 A; T _j = 150 °C; <u>Fig. 6</u>	- 1.3 2		2	V	
Dynamic	characteristics						
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 200 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7		-	12	18	ns

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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	
2	Α	anode		K — A 001aaa020
mb	mb	mounting base; connected to cathode	1 2 TO-220AC (SOD59)	001aaa020

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BYC10-600P	TO-220AC	plastic single-ended package; heatsink mounted; 1 mounting hole; 2-lead TO-220AC	SOD59			

7. Marking

Table 4. Marking codes

Type number	Marking codes
BYC10-600P	BYC10-600P

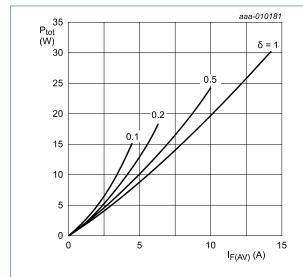
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8. Limiting values

Table 5. Limiting values

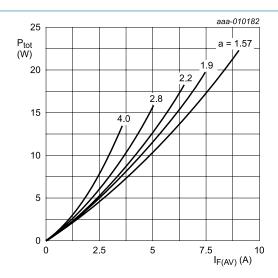
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		600	V
V_{RWM}	crest working reverse voltage		600	V
V_R	reverse voltage	DC	600	V
I _{F(AV)}	average forward current	$δ = 0.5$; $T_{mb} \le 127$ °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	10	А
I _{FRM}	repetitive peak forward current	δ = 0.5; t _p = 25 μs; T _{mb} ≤ 127 °C; square-wave pulse	20	Α
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	150	Α
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	165	Α
T _{stg}	storage temperature		-65 to 175	°C
T _j	junction temperature		175	°C



 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$ $V_o = 1.572 \text{ V; R}_s = 0.040 \Omega$ Fig. 1. Forward power dissipation as a fu





a = form factor = $I_{F(RMS)}/I_{F(AV)}$ V_o = 1.572 V; R_s = 0.040 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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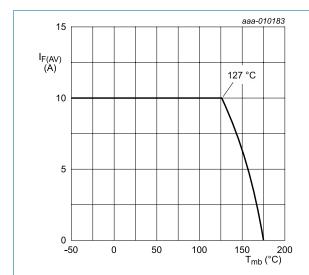


Fig. 3. Forward current as a function of mounting base temperature; maximum values

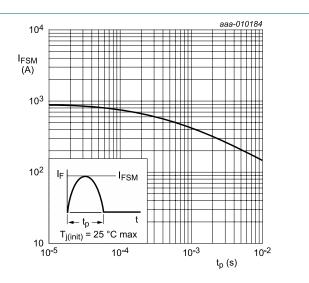


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	with heatsink compound; Fig. 5	-	-	2	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient	in free air	-	60	-	K/W

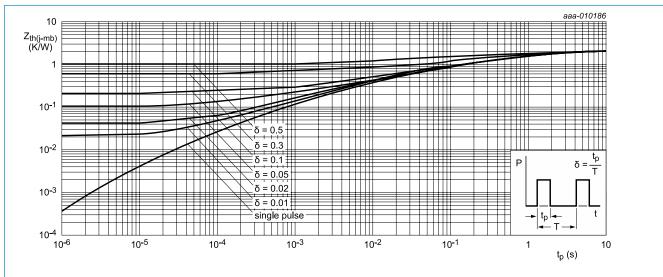


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

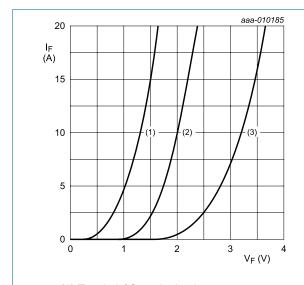
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10. Characteristics

Table 7 Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V_{F}	forward voltage	I _F = 10 A; T _j = 25 °C; <u>Fig. 6</u>	-	2.5	3.2	V
		I _F = 10 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.3	2	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	-	10	μA
		V _R = 600 V; T _j = 150 °C	-	-	0.8	mA
Dynamic	characteristics					
Q _r	recovered charge	$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_J = 25 \text{ °C}; Fig. 7$	-	26	-	nC
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ μ s; $T_j = 125 ^{\circ}\text{C}; Fig. 7$	-	83	-	nC
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	12	18	ns
		$I_F = 10 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	19	-	ns
		$I_F = 10 \text{ A}$; $V_R = 200 \text{ V}$; $dI_F/dt = 200 \text{ A/}\mu\text{s}$; $T_J = 25 ^{\circ}\text{C}$; Fig. 7	-	26	-	ns
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$	-	34	-	ns
I _{RM}	peak reverse recovery current	$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	2	-	А
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A/}\mu\text{s};$ $T_i = 125 \text{ °C}; Fig. 7$	-	4.8	-	Α



(1) T_j = 150 °C; typical values (2) T_j = 150 °C; maximum values

(3) $T_j = 25 \,^{\circ}\text{C}$; maximum values $V_0 = 1.572 \,\text{V}$; $R_s = 0.040 \,\Omega$

Fig. 6. Forward current as a function of forward voltage

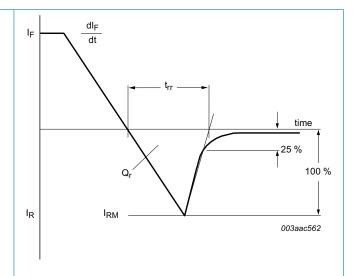
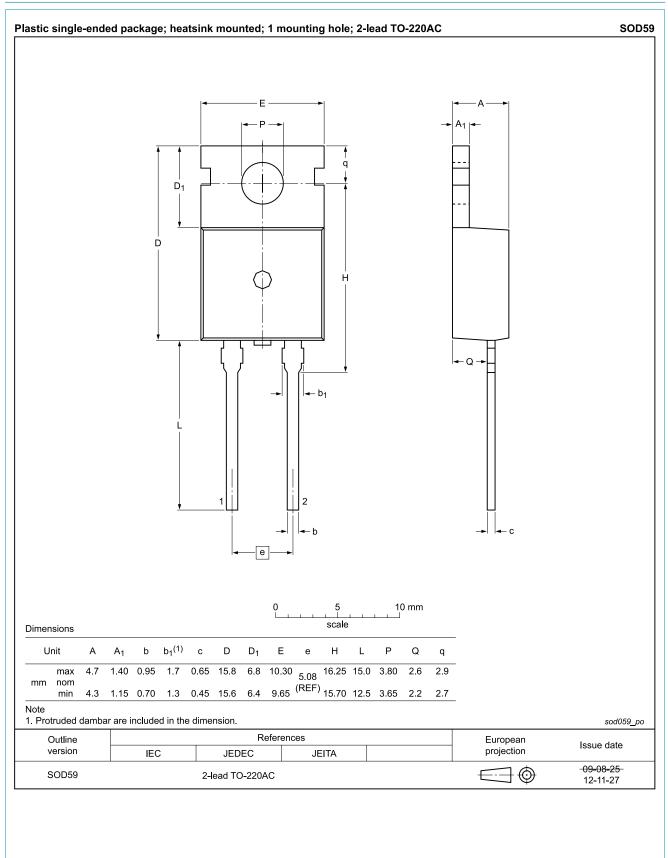


Fig. 7. Reverse recovery definitions; ramp recovery

11. Package outline



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12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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BYC10-600P

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